

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	74HC595D
▶ Overseas	Part Number	74HC595D
▶ Equivalent	Part Number	74HC595D

EV is the abbreviation of name EVVO

8-bit serial-in/serial or parallel-out shift register with output latches; 3-state

Description :

74HC595 is a high-speed silicon gate CMOS device with pins compatible with low-power Schottky TTL circuits (LSTTL). It complies with JEDEC standard No.7A. It consists of eight serial shift registers with storage registers and three state outputs. The shift register and storage register have separate clocks. Data in shift clock SH_ When the rising edge of CP arrives, shift transmission is performed, while the storage clock ST_

When the rising edge of CP arrives, it is transferred from the shift register to the storage register. If two clocks are connected together, the data on the shift register is always one clock pulse ahead of the storage register. The shift register has a serial input (DS) and a cascaded serial output (Q7'), as well as an asynchronous reset (effective at low levels).

The storage register has an eight bit parallel bus driver output with a three state output. When the output enable end (OE) is at low level, the output end is normal output. Conversely, when OE is at high level, the output is in high resistance off state.

Features :

- Eight bit serial input
- Eight bit serial or parallel output
- Shift output frequency ESD protection function at 100MHz (typical value)
- A storage register with a three state output and a shift register with direct zeroing

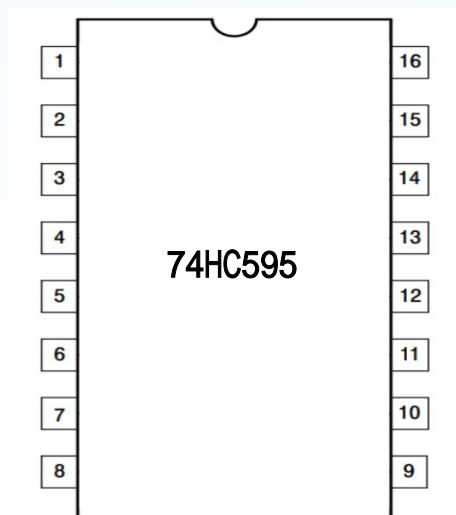
Application :

- serial parallel conversion
- Remote control memory retention device

Absolute Maximum Ratings

parameter	symbol	Test conditions	min	max	unit
supply voltage	Vcc		-0.5	7	V
Input diode current	I _{IK}	V _I < -0.5V or V _I > Vcc + 0.5V	-	±20	mA
Output diode current	I _{oK}	V _o < -0.5V or V _o > Vcc + 0.5V	-	±20	mA
Output pouring current or pulling current	I _o	-0.5V < V _o < Vcc + 0.5V	-		
		Q' standard output	-	±25	mA
		Q0~Q7 bus drive output	-	±35	mA
Vcc, GND current	I _{cc} , I _{IGND}		-	±70	mA
storage temperature	T _{stg}		-65	150	°C
consumption	P _{tot}	T _{amb} = -40 to 125°C	-	500	mW

Pin Assignment :



DIP/SOP16

pin no.	symbol	function description
1	Q1	Parallel output terminal
2	Q2	Parallel output terminal
3	Q3	Parallel output terminal
4	Q4	Parallel output terminal
5	Q5	Parallel output terminal
6	Q6	Parallel output terminal
7	Q7	Parallel output terminal
8	GND	grounding (0V)
9	Q7'	Serial output terminal
10	$\overline{\text{MR}}$	Main reset (effective at low level)
11	SH_CP	Shift register clock input
12	ST_CP	Memory register clock input terminal
13	$\overline{\text{OE}}$	Output enabling terminal (effective at low level)
14	DS	Serial input terminal
15	Q0	Parallel output terminal
16	Vcc	power supply

menubar

input					output		function
SH_CP	ST_CP	\overline{OE}	\overline{MR}	DS	Q7'	Qn	
×	×	L	L	×	L	n. c	MR only resets the shift register when the power level is low
×	↑	L	L	×	L	L	Shift register transfers null values to storage registers
×	×	H	L	×	L	Z	Clear the shift register to zero; Parallel output in
↑	×	L	H	H	Q6'	n. c	The logic high level is transmitted from the input to the shift register of segment 0; The data of all shift registers is sequentially transmitted under the action of the shift clock
×	↑	L	H	×	n. C,	Qn'	All shift register data is transmitted to the corresponding storage registers under the action of the storage clock
↑	↑	L	H	×	Q6'	Qn'	The shift register is sequentially passed back; Simultaneously shifting the register to transfer the previous state to the corresponding storage register and output

Note: H=high level L=low level falling edge rising edge
Z=high resistance closed state n.c.=no change
X=irrelevant quantity

function diagram

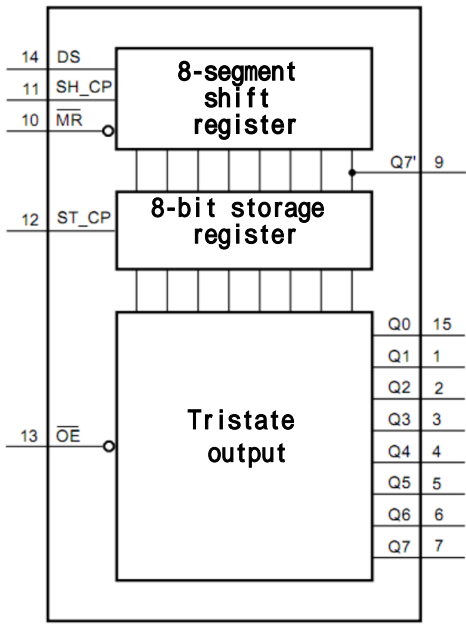


Figure 3 Functional Diagram

logic diagram

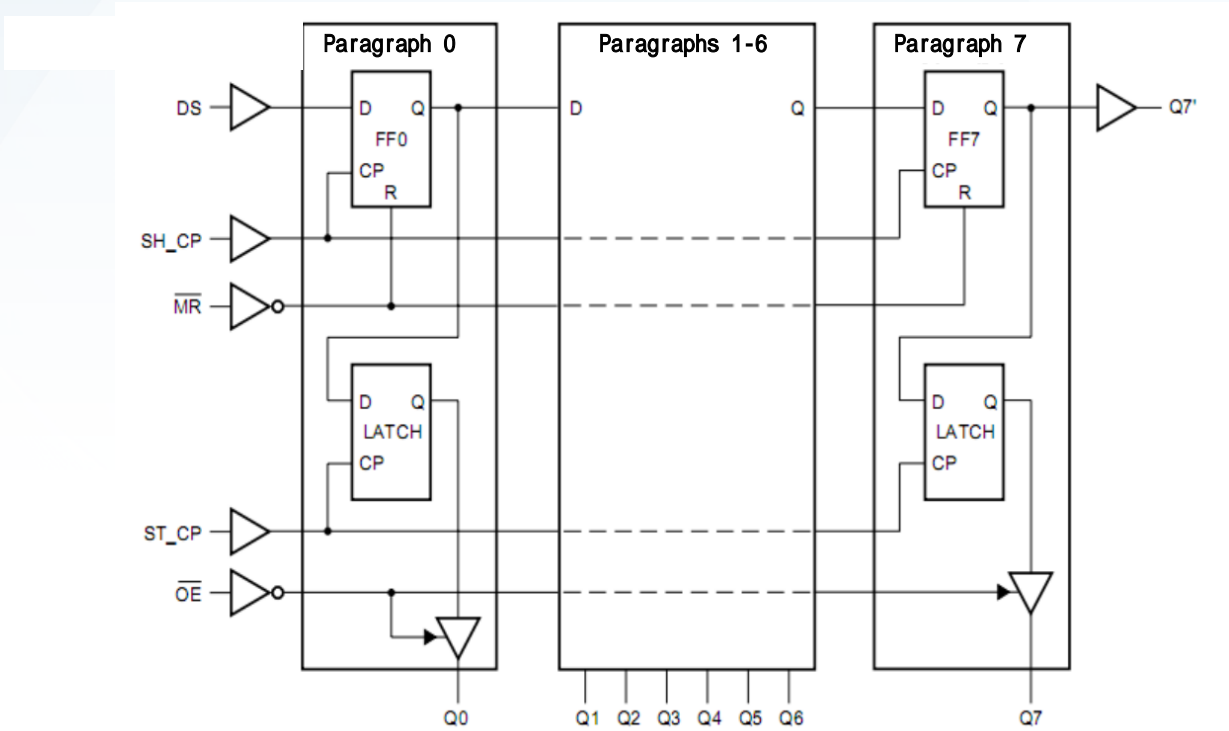


Figure 4 Logic Diagram

Timing Diagram

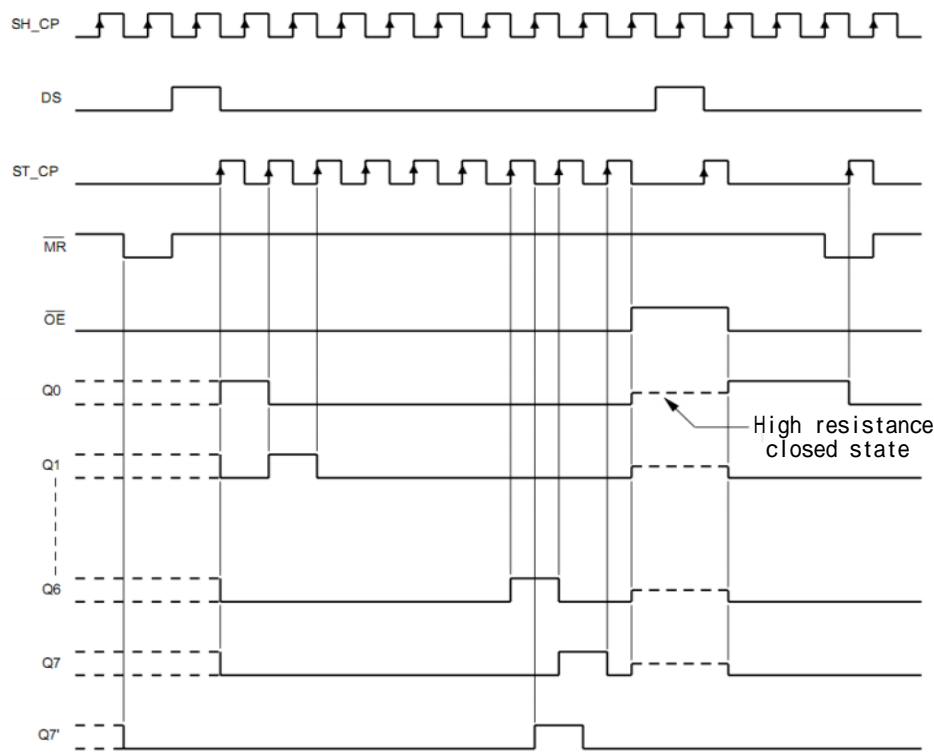


Figure 5 Timing Chart

DC parameters (ambient temperature: -40~+125 ; all typical values are tested at 25)

parameter	symbol	Test conditions		min	typ	max	unit
		condition	V _{CC} (V)				
High Level Input Voltage	VIH		2	1.5	1.2	—	V
			4.5	3.15	2.4	—	V
			6	4.2	3.2	—	V
low level input voltage	VIL		2	—	0.8	0.5	V
			4.5	—	2.1	1.35	V
			6	—	2.8	1.8	V
high level output voltage	VOH	VI=VIH or VIL					
		All outputs I _O =-20uA	2	1.9	2	—	V
			4.5	4.4	4.5	—	V
			6	5.9	6	—	V
		Q7' Standard output terminal I _O =-4.0mA I _O =-5.2mA	4.5	3.84	4.32	—	V
			6	5.34	5.81	—	V
		Qn bus drive output I _O =-6.0mA I _O =-7.8mA	4.5	3.84	4.32	—	V
			6	5.34	5.81	—	V
Low Level Output Voltage	VOL	VI=VIH or VIL					
		All outputs I _O =-20uA	2	—	0	0.1	V
			4.5	—	0	0.1	
			6	—	0	0.1	
		output terminal I _O =-4.0mA I _O =-5.2mA	4.5	—	0.15	0.33	V
			6	—	0.16	0.33	
		output I _O =-6.0mA I _O =-7.8mA	4.5	—	0.16	0.33	V
			6	—	0.16	0.33	
Input peak current	IL	VI=V _{CC} or GND	6	—	—	±1	uA
Three state output high resistance current	I _{OZ}	VI=VIH or VIL Vo=V _{CC} or GND	6	—	—	±5	uA
Static power supply current	I _{CC}	VI=V _{CC} or GND I _O =0	6	—	—	80	uA

ambient temperature: -40 ~+125

parameter	symbol	Test conditions		min	typ	max	unit
		condition	V _{CC} (V)				
High Level Input Voltage	VIH		2	1.5	-	-	V
			4.5	3.15	-	-	V
			6	4.2	-	-	V
low level input voltage	VIL		2	-	-	0.5	V
			4.5	-	-	1.35	V
			6	-	-	1.8	V
high level output voltage	VOH	VI=VIH or VIL					
		ALL outputs I _O =-20uA	2	1.9	-	-	V
			4.5	4.4	-	-	V
			6	5.9	-	-	V
		Q7' Standard output terminal I _O =-4.0mA I _O =-5.2mA	4.5	3.7	-	-	V
			6	5.2	-	-	V
		Qn bus drive output I _O =-6.0mA I _O =-7.8mA	4.5	3.7	-	-	V
			6	5.2	-	-	V
Low Level Output Voltage	VOL	VI=VIH or VIL					
		ALL outputs I _O =-20uA	4.5	-	-	0.1	V
		Q7' Standard output terminal I _O =-4.0mA	4.5	-	-	0.4	V
		Qn bus drive output I _O =-6.0mA	4.5	-	-	0.4	V
Input peak current	ILI	VI=V _{CC} or GND	5.5	-	-	±1	uA
Three state output high resistance current	I _{OZ}	VI=VIH or VIL Vo=V _{CC} or GND	5.5	-	-	±10	uA
Static power supply current	I _{CC}	VI=V _{CC} or GND I _O =0	5.5	-	-	160	uA

AC parameters (GND=0V; t_r - t_f -6ns ; CL=50Pf)

ambient temperature : 25

parameter	symbol	Test conditions		min	typ	max	unit
		wave form	V _{CC} (V)				
Transmission delay time from SH_CP to Q7’	tPHL/tPLH	See Figure 6	2	–	52	160	ns
			4.5	–	19	32	ns
			6	–	15	27	ns
ST_CP to Qn transmission delay time		See Figure 7	2	–	55	175	ns
			4.5	–	20	35	ns
			6	–	16	30	ns
Transmission delay time from MR to Q7’	tPHL	See Figure 9	2	–	47	175	ns
			4.5	–	17	35	ns
			6	–	14	30	ns
OE causes Qn terminal to transition from high resistance state to enable output time	tPZH/tPZL	See Figure 10	2	–	47	30	ns
			4.5	–	17	150	ns
			6	–	14	30	ns
OE enables the Qn terminal to output from enable to high resistance state time	tPHZ/tPLZ	See Figure 10	2	–	41	26	ns
			4.5	–	15	150	ns
			6	–	12	30	ns
Shift clock pulse width (high or low level)	tW	See Figure 6	2	75	17	26	ns
			4.5	15	6	–	ns
			6	13	5	–	ns
Store clock pulse width (high or low level)		See Figure 7	2	75	11	–	ns
			4.5	15	4	–	ns
			6	13	3	–	ns
Main reset pulse width (low level)		See Figure 9	2	75	17	–	ns
			4.5	15	6	–	ns
			6	13	5	–	ns
Establishment time from DS to SH_CP	tsu	See Figure 8	2	50	11	–	ns
			4.5	10	4	–	ns
			6	9	3	–	ns
Establishment time from SH_CP to ST_CP		See Figure 7	2	75	22	–	ns
			4.5	15	8	–	ns
			6	13	7	–	ns
DS to SH_CP retention time	th	See Figure 8	2	3	–6	–	ns
			4.5	3	–2	–	ns
			6	3	–2	–	ns
MR enables SH CP reset time	trem	See Figure 9	2	50	–19	–	ns
			4.5	10	–7	–	ns
			6	9	–6	–	ns
Minimum clock pulse width of SH_CP or ST_CP	fmax	See Figure 6, 7	2	9	30	–	MHZ
			4.5	30	91	–	MHZ
			6	35	108	–	MHZ

ambient temperature : -40 ~85

parameter	symbol	Test conditions		min	typ	max	unit
		wave form	Vcc(V)				
Transmission delay time from SH_CP to Q7'	tPHL/tPLH	See Figure 6	2	–	–	200	ns
			4.5	–	–	40	ns
			6	–	–	34	ns
ST_ CP to Qn transmission delay time		See Figure 7	2	–	–	220	ns
			4.5	–	–	44	ns
			6	–	–	37	ns
Transmission delay time from MR to Q7'	tPHL	See Figure 9	2	–	–	220	ns
			4.5	–	–	44	ns
			6	–	–	37	ns
OE causes Qn terminal to transition from high resistance state to enable	tPZH/tPZL	See Figure 10	2	–	–	190	ns
			4.5	–	–	38	ns
			6	–	–	33	ns
OE enables the Qn terminal to output from enable to high resistance	tPHZ/tPLZ	See Figure 10	2	–	–	190	ns
			4.5	–	–	38	ns
			6	–	–	33	ns
Shift clock pulse width (high or low level)	tW	See Figure 6	2	95	–	–	ns
			4.5	19	–	–	ns
			6	16	–	–	ns
Store clock pulse width (high or low level)		See Figure 7	2	95	–	–	ns
			4.5	19	–	–	ns
			6	16	–	–	ns
Main reset pulse width (low level)		See Figure 9	2	95	–	–	ns
			4.5	19	–	–	ns
			6	16	–	–	ns
Establishment time from DS to SH_ CP	tsu	See Figure 8	2	65	–	–	ns
			4.5	13	–	–	ns
			6	11	–	–	ns
Establishment time from SH_ CP to ST_ CP		See Figure 7	2	95	–	–	ns
			4.5	19	–	–	ns
			6	16	–	–	ns
DS to SH_ CP retention time	th	See Figure 8	2	3	–	–	ns
			4.5	3	–	–	ns
			6	3	–	–	ns
MR enables SH_ CP reset time	trem	See Figure 9	2	65	–	–	ns
			4.5	13	–	–	ns
			6	11	–	–	ns
Minimum clock pulse width of SH_ CP or ST_ CP	fmax	See Figure 6, 7	2	4.8	–	–	MHZ
			4.5	24	–	–	MHZ
			6	28	–	–	MHZ

ambient temperature : -40 ~125

parameter	symbol	Test conditions		min	typ	max	unit
		wave form	V _{CC} (V)				
Transmission delay time from SH_ CP to Q7’	tPHL/tPLH	See Figure 6	2	-	-	240	ns
			4.5	-	-	48	ns
			6	-	-	41	ns
ST_ CP to Qn transmission delay time		See Figure 7	2	-	-	265	ns
			45	-	-	53	ns
			6	-	-	45	ns
Transmission delay time from MR to Q7’	tPHL	See Figure 9	2	-	-	265	ns
			4.5	-	-	53	ns
			6	-	-	45	ns
OE causes Qn terminal to transition from high resistance state to enable	tPZH/tPZL	See Figure 10	2	-	-	225	ns
			4.5	-	-	45	ns
			6	-	-	35	ns
OE enables the Qn terminal to output from enable to high resistance	tPHZ/tPLZ	See Figure 10	2	-	-	225	ns
			4.5	-	-	45	ns
			6	-	-	35	ns
Shift clock pulse width (high or low level)	tW	See Figure 6	2	110	-	-	ns
			4.5	22	-	-	ns
			6	19	-	-	ns
Store clock pulse width (high or low level)		See Figure 7	2	110	-	-	ns
			4.5	22	-	-	ns
			6	19	-	-	ns
Main reset pulse width (low level)		See Figure 9	2	110	-	-	ns
			4.5	22	-	-	ns
			6	19	-	-	ns
Establishment time from DS to SH_ CP	tsu	See Figure 8	2	75	-	-	ns
			4.5	15	-	-	ns
			6	13	-	-	ns
Establishment time from SH_ CP to ST_ CP		See Figure 7	2	110	-	-	ns
			4.5	22	-	-	ns
			6	19	-	-	ns
DS to SH_ CP retention time	th	See Figure 8	2	3	-	-	ns
			4.5	3	-	-	ns
			6	3	-	-	ns
MR enables SH_ CP reset time	trem	See Figure 9	2	75	-	-	ns
			4.5	15	-	-	ns
			6	13	-	-	ns
Minimum clock pulse width of SH_ CP or ST _ CP	fmax	See Figure 6, 7	2	4	-	-	MHZ
			4.5	20	-	-	MHZ
			6	24	-	-	MHZ

AC waveform

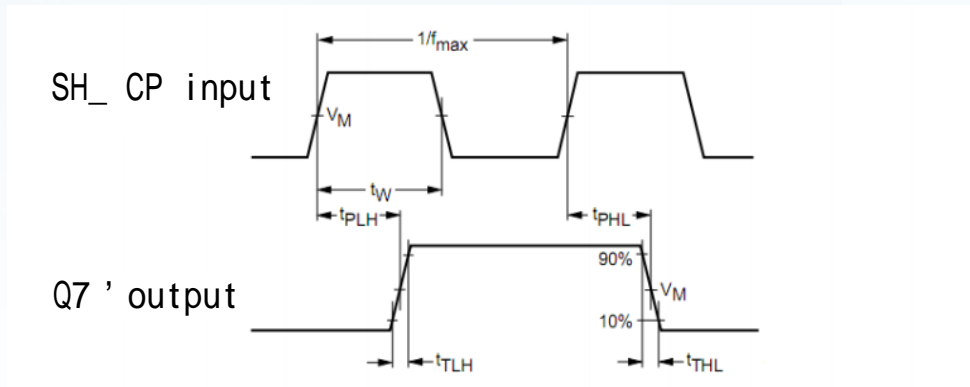


Figure 6: The above figure shows the transmission delay time, shift clock pulse width, and maximum shift clock frequency from shift clock (SH_CP) to output (Q7 ')

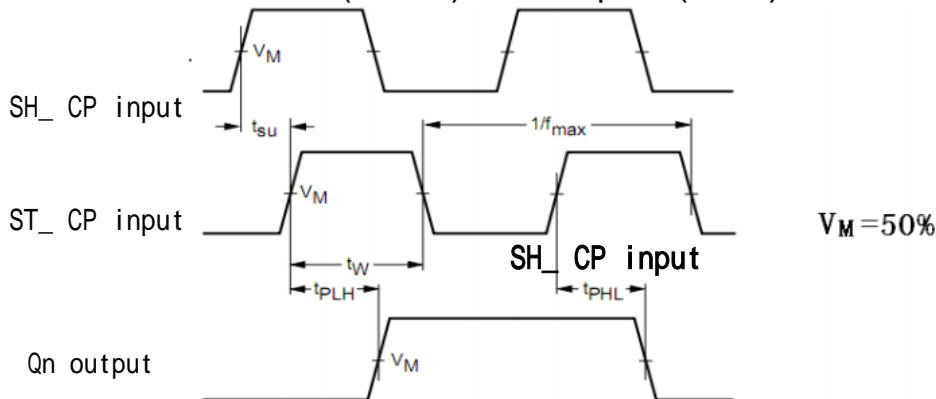


Figure 7: The above figure shows the transmission delay time from storage clock (ST_CP) to output (Qn), storage clock pulse width, and establishment time from shift clock to storage clock

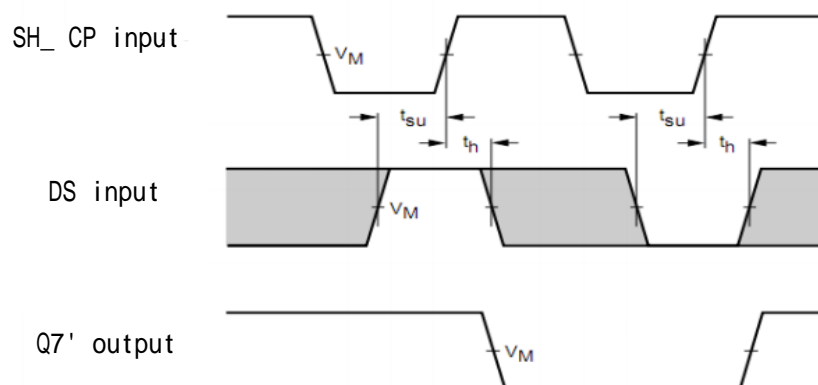


Figure 8: The above figure shows the establishment and retention time of DS input
 Note: The shaded portion indicates that the input signal has no effect on the output at this time

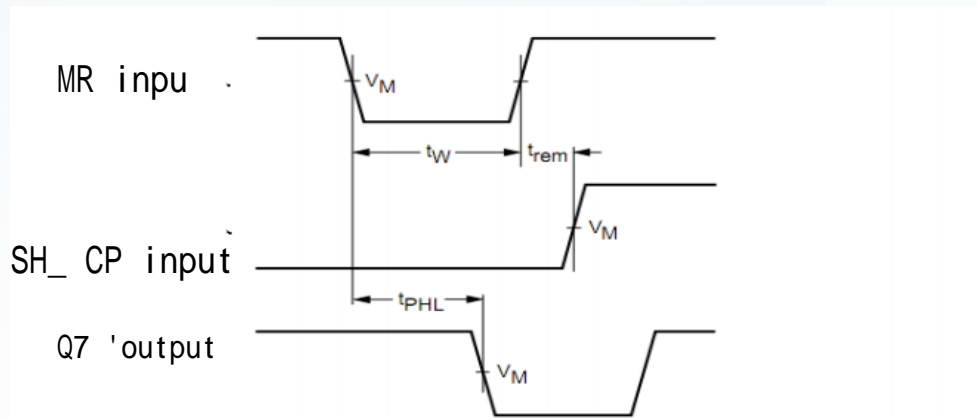


Figure 9: The above figure shows the pulse width of the main reset (MR), the transmission delay time from the main reset to the output (Q7'), and the reset time from the main reset to the shift clock (SH_CP)

Qn output:
From low level to high
resistance state, from
high
resistance state to

low level Qn output:
From high level to
high
resistance state, from
high
resistance state to
high level

OE input

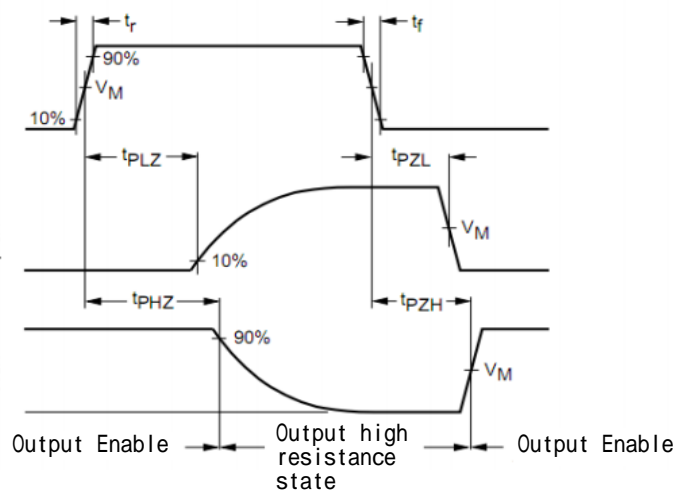
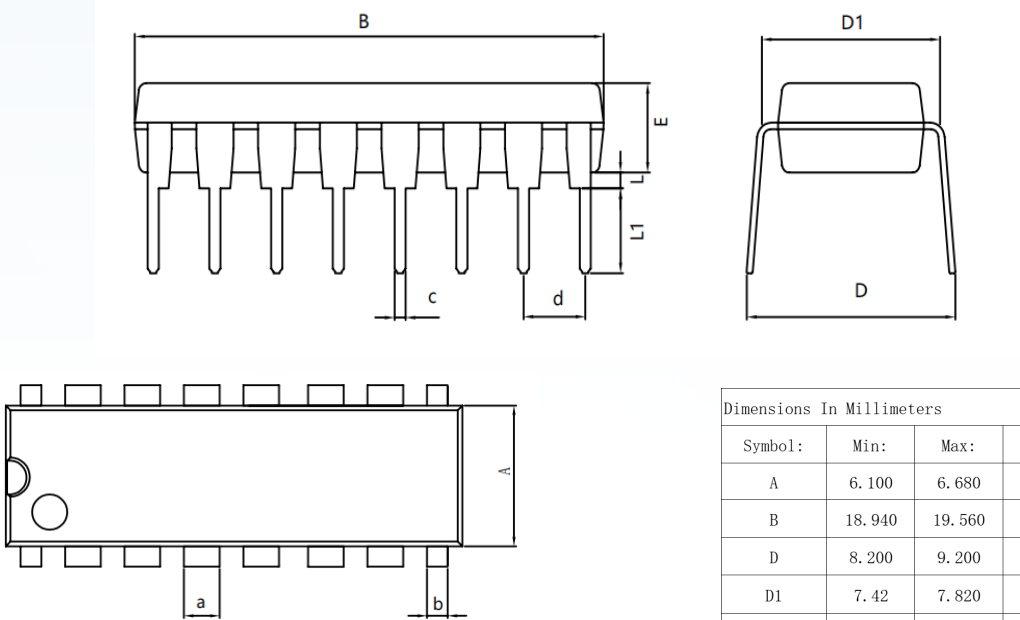


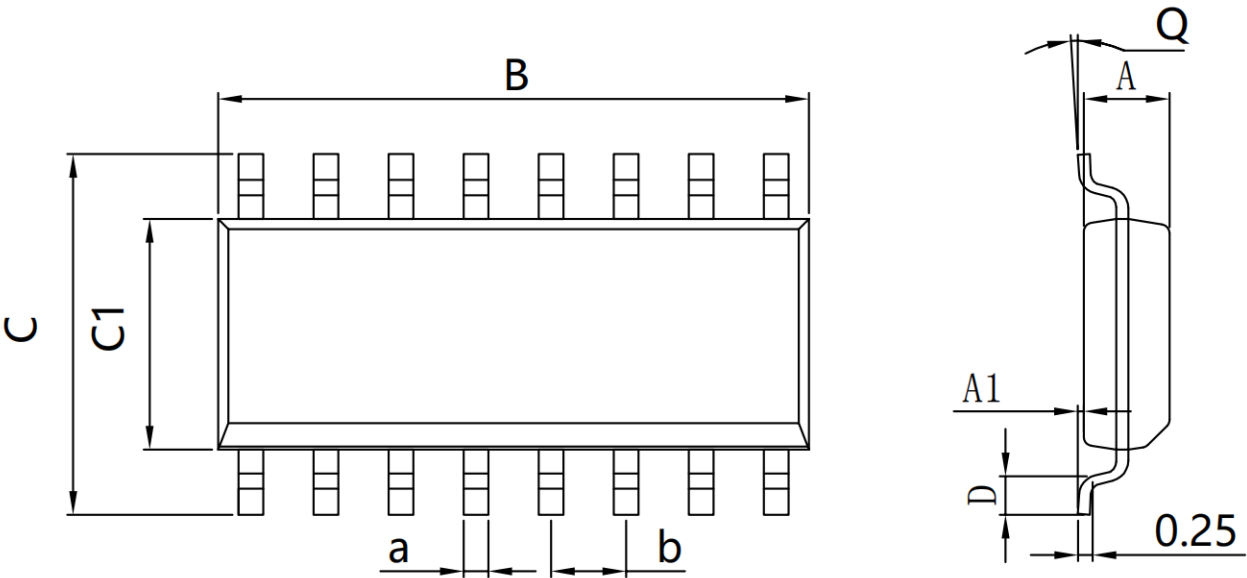
Figure 10: The above figure shows the variation time of the three state output with the output enable end

Pin Assignment :
DIP16



Dimensions In Millimeters					
Symbol:	Min:	Max:	Symbol:	Min:	Max:
A	6.100	6.680	L	0.500	0.800
B	18.940	19.560	a	1.524 TYP	
D	8.200	9.200	b	0.889 TYP	
D1	7.42	7.820	C	0.457 TYP	
E	3.100	3.550	d	2.540 TYP	
L	0.500	0.800			

SOP16



Dimensions In Millimeters					
Symbol:	Min:	Max:	Symbol:	Min:	Max:
A	1.225	1.570	D	0.400	0.950
A1	0.100	0.250	Q	0°	8°
B	9.800	10.00	a	0.420 TYP	
C	5.800	6.250	b	1.270 TYP	
C1	3.800	4.000			

Disclaimer

EVVOSEMI ("EVVO") reserves the right to make corrections, enhancements, improvements, and other changes to its products and services at any time, and to discontinue any product or service without notice.

EVVO warrants the performance of its hardware products to the specifications applicable at the time of sale in accordance with its standard warranty. Testing and other quality control techniques are used as deemed necessary by EVVO to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

Customers should obtain and confirm the latest product information and specifications before final design, purchase, or use. EVVO makes no warranty, representation, or guarantee regarding the suitability of its products for any particular purpose, nor does EVVO assume any liability for application assistance or customer product design. EVVO does not warrant or accept any liability for products that are purchased or used for any unintended or unauthorized application.

EVVO products are not authorized for use as critical components in life support devices or systems without the express written approval of EVVOSEMI.

The EVVO logo and EVVOSEMI are trademarks of EVVOSEMI or its subsidiaries in relevant jurisdictions. EVVO reserves the right to make changes without further notice to any products herein.